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1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9560Z

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability
- High collector current gain h_{FE} at high I_C
- AEC-Q101 qualified

3. Applications

- Electronic ballast for fluorescent lighting
- · LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	600	V
I _C	collector current		_	-	0.5	Α
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 50 mA; T_{amb} = 25 °C	70	135	-	





600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	E	emitter		. 1
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym016

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV8560Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes

3	
Type number	Marking code
PBHV8560Z	HV856Z

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

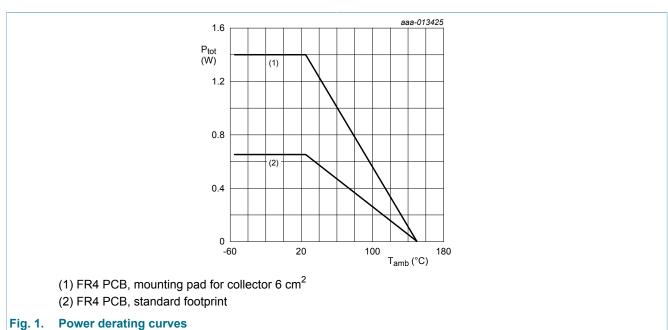
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	600	V
V_{CEO}	collector-emitter voltage	open base		-	600	V
V_{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	600	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			<u>[2]</u>	-	1.4	W
T_{j}	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



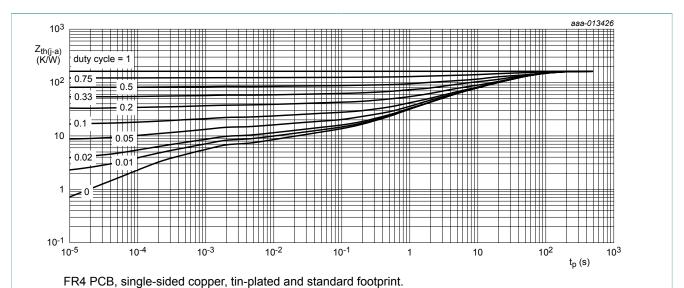
600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

Thermal characteristics

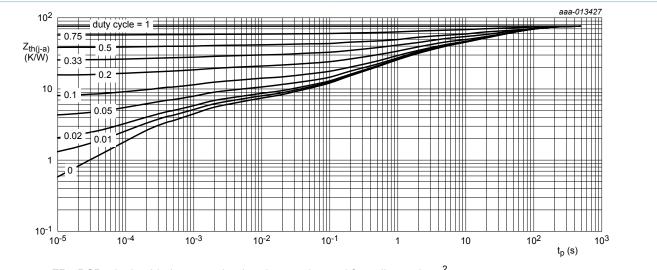
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
and a)	thermal resistance from junction to ambient	in free air	[1]	-	-	190	K/W
			[2]	-	-	89	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

PBHV8560Z

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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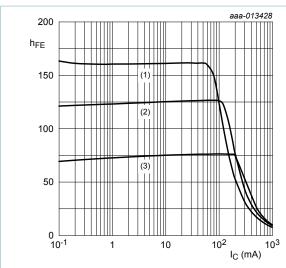
600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 400 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 400 V; I _E = 0 A; T _j = 150 °C	-	-	10	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 400 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C	70	135	-	
		$V_{CE} = 10 \text{ V}; I_{C} = 100 \text{ mA}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	70	135	-	
V _{CEsat}	collector-emitter	I_C = 50 mA; I_B = 5 mA; T_{amb} = 25 °C	-	50	100	mV
	saturation voltage	I_{C} = 100 mA; I_{B} = 20 mA; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	50	100	mV
V _{BEsat}	base-emitter saturation voltage	I_{C} = 50 mA; I_{B} = 5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	950	mV
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	7.5	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	710	-	pF

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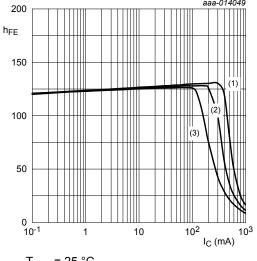
$$V_{CE} = 10 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig. 4. DC current gain as a function of collector current; typical values



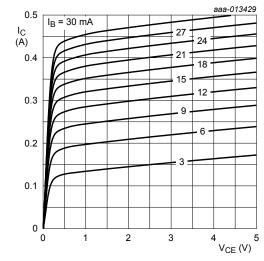
$$T_{amb}$$
 = 25 °C

(1)
$$V_{CE} = 10 \text{ V}$$

(2)
$$V_{CE} = 25 \text{ V}$$

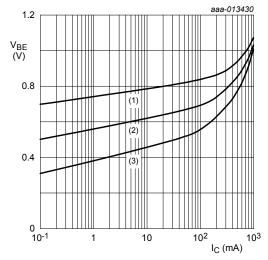
(3)
$$V_{CE} = 50 \text{ V}$$

Fig. 5. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



(1)
$$T_{amb} = -55 \, ^{\circ}C$$

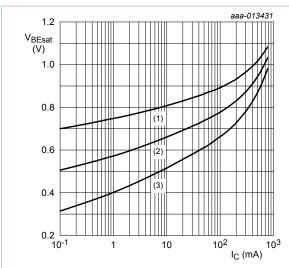
(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values

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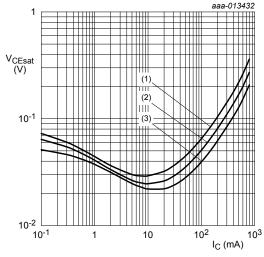


$$I_C/I_B = 5$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb}$$
= 100 °C



$$I_C/I_B = 5$$

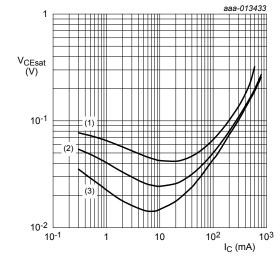
(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

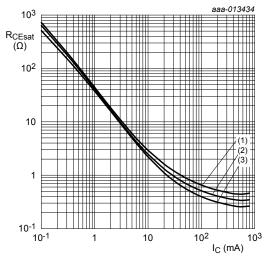


(1)
$$I_C/I_B = 10$$

(2)
$$I_C/I_B = 5$$

(3)
$$I_C/I_B = 2.5$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

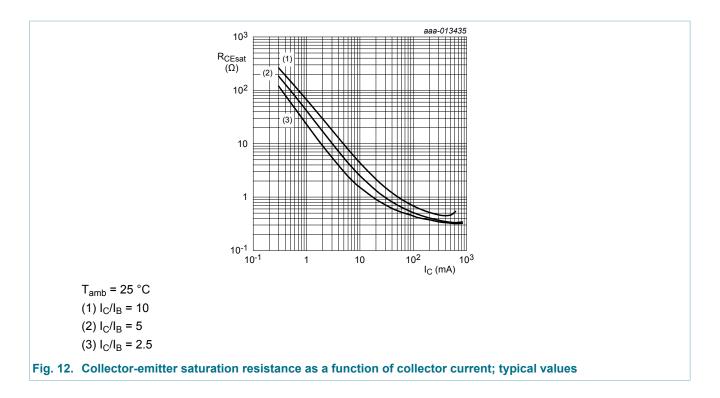
(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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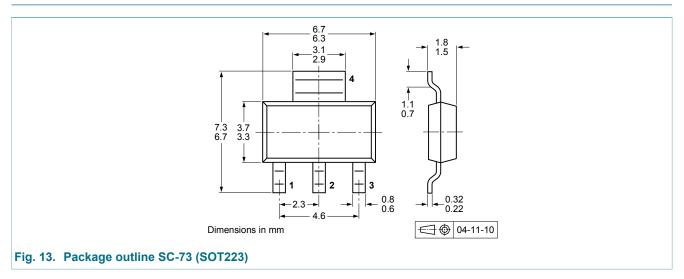


11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



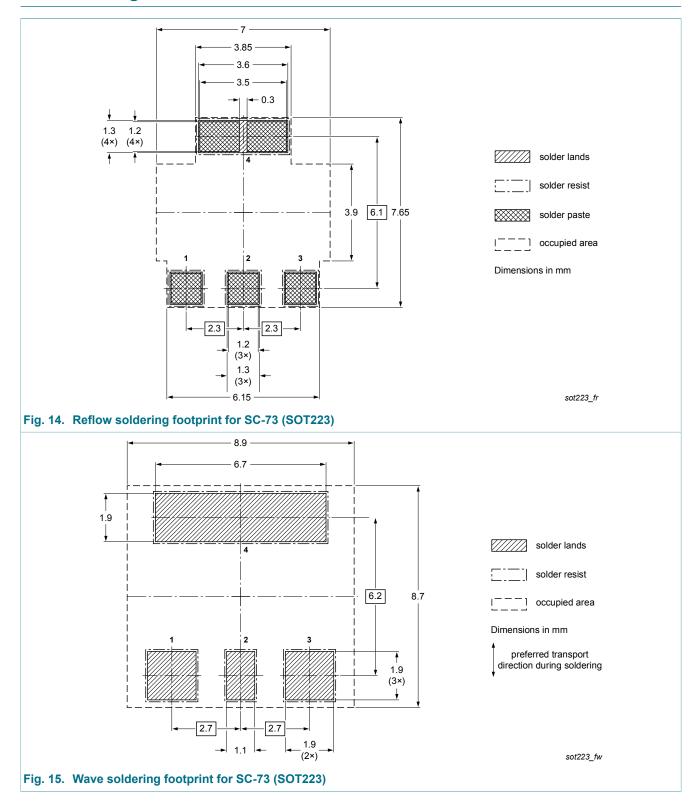
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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8560Z v.1	20150313	Product data sheet	-	-

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

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